

R-C Thermal Model Parameters

DESCRIPTION

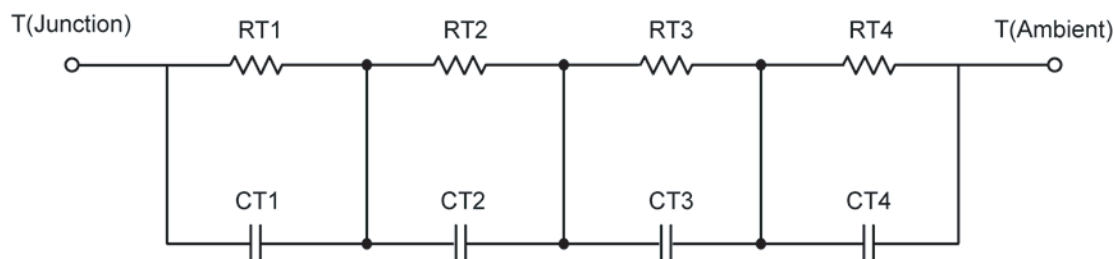
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

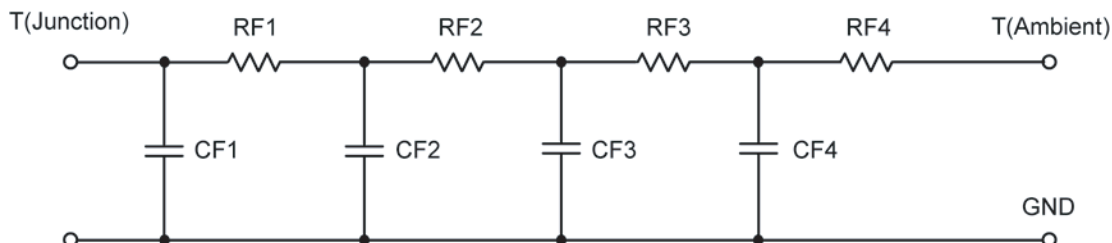
For a detailed explanation of implementing these values in P-Spice, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-Spice Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	184.8122	N/A	N/A
RT2	73.5199	N/A	N/A
RT3	51.4162	N/A	N/A
RT4	190.2517	N/A	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	3.2316 m	N/A	N/A
CT2	309.6678 u	N/A	N/A
CT3	1.0575	N/A	N/A
CT4	10.5491 m	N/A	N/A

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	75.0796	N/A	N/A
RF2	142.6818	N/A	N/A
RF3	228.9242	N/A	N/A
RF4	53.3144	N/A	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	240.7669 u	N/A	N/A
CF2	1.4061 m	N/A	N/A
CF3	3.6853 m	N/A	N/A
CF4	883.2685 m	N/A	N/A

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

